## 2SB1494

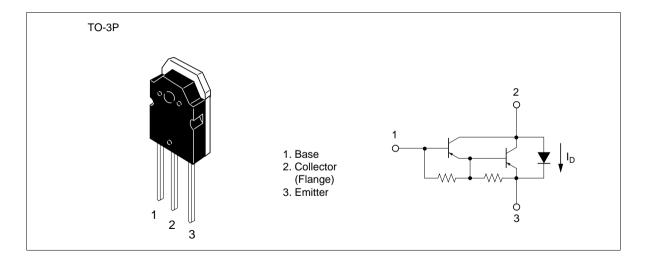
## Silicon PNP Triple Diffused

# **HITACHI**

#### **Application**

Low frequency power amplifier complementary Pair with 2SD2256

#### Outline





### 2SB1494

### **Absolute Maximum Ratings** (Ta = 25°C)

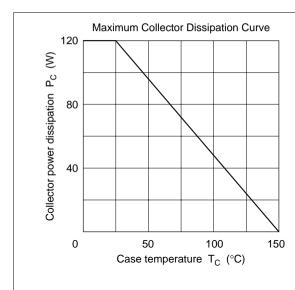
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	-120	V
Collector to emitter voltage	V <sub>CEO</sub>	-120	V
Emitter to base voltage	V <sub>EBO</sub>	<b>–</b> 7	V
Collector current	I <sub>c</sub>	<b>–</b> 25	A
Collector peak current	I <sub>C(peak)</sub>	-35	A
Collector power dissipation	P <sub>c</sub> *1	120	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
C to E diode forward current	I <sub>D</sub> *1	25	A

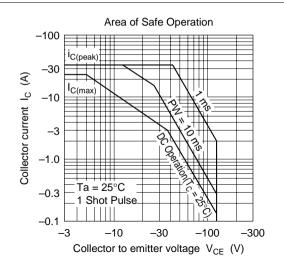
Note: 1. Value at  $T_c = 25^{\circ}C$ .

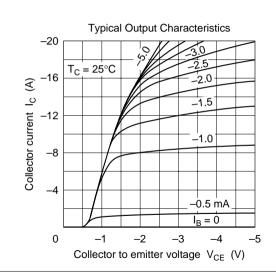
### **Electrical Characteristics** (Ta = 25°C)

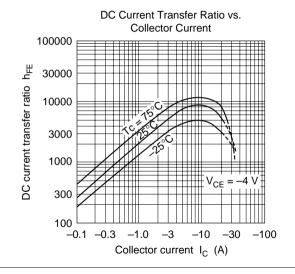
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	_	_	V	$I_{\rm C} = -0.1 \text{ mA}, I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{\text{C}} = -25 \text{ mA}, R_{\text{BE}} = \infty$
Collector to emitter sustain voltage	$V_{\text{CEO(sus)}}$	-120	_	_	V	$I_{\rm C}$ = -200 mA, $R_{\rm BE}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	<b>-7</b>	_	_	V	$I_{\rm E} = -50 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-10	μΑ	$V_{CB} = -100 \text{ V}, I_{E} = 0$
	I <sub>CEO</sub>	_	_	-10		$V_{CE} = -100 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	h <sub>FE1</sub>	2000	_	20000		$V_{CE} = -4 \text{ V}, I_{C} = -12 \text{ A}^{*1}$
	h <sub>FE2</sub>	500	_	_		$V_{CE} = -4 \text{ V}, I_{C} = -25 \text{ A}^{*1}$
Collector to emitter saturation	V <sub>CE(sat)1</sub>	_	_	-2.0	V	$I_{\rm C} = -12 \text{ A}, I_{\rm B} = -24 \text{ mA}^{*1}$
voltage	V <sub>CE(sat)2</sub>	_	_	-3.5		$I_{\rm C} = -25 \text{ A}, I_{\rm B} = -250 \text{ mA}^{*1}$
Base to emitter saturation	$V_{\text{BE}(\text{sat})1}$	_	_	-3.0	V	$I_{\rm C} = -12 \text{ A}, I_{\rm B} = -24 \text{ mA}$
voltage	$V_{BE(sat)2}$	_	_	-4.5		$I_{\rm C} = -25 \text{ A}, I_{\rm B} = -250 \text{ mA}^{*1}$

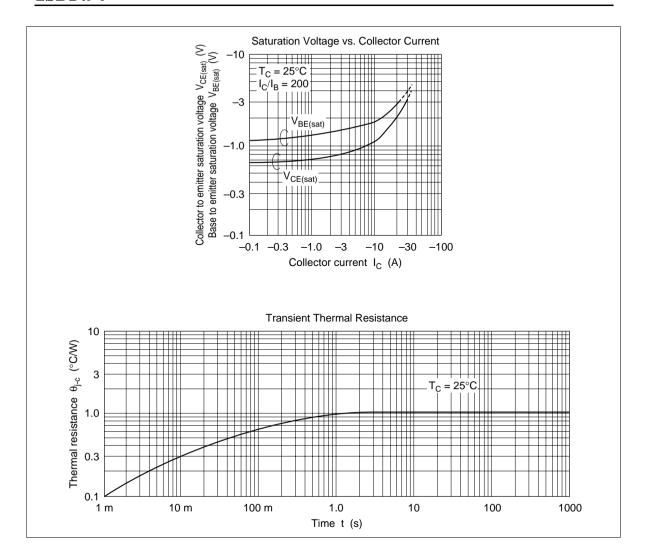
Note: 1. Pulse test.



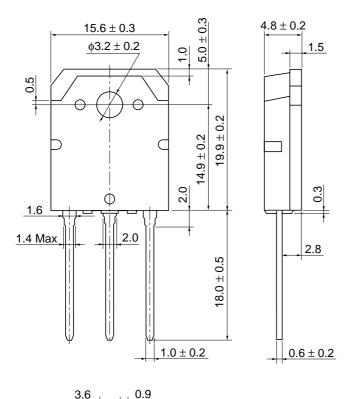


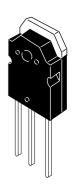






Unit: mm





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5.45 ± 0	0.5					5.4	45 ±	0.5

Hitachi Code	TO-3P
JEDEC	
EIAJ	Conforms
Weight (reference value)	5.0 g

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## HTACHI

#### Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322 Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218

Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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